

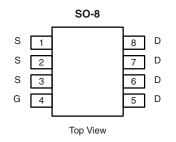
## VS5806AS-VB Datasheet N-Channel 60 V (D-S) 175 °C MOSFET

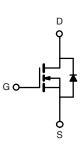
PRODUCT SUMMARY					
V <sub>DS</sub> (V)	60				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 V$	0.0048				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 6 V$	0.006				
I <sub>D</sub> (A)	16				
Configuration	Single				

#### FEATURES

- Trench Power MOSFET
- 100 %  $R_g$  and UIS Tested







N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V <sub>DS</sub>	60	V		
Gate-Source Voltage		V <sub>GS</sub> ± 20		V		
Continuous Drain Current	T <sub>C</sub> = 25 °C	1	16			
	T <sub>C</sub> = 125 °C	I <sub>D</sub>	9			
Continuous Source Current (Diode Conduction)		I <sub>S</sub>	6	A		
Pulsed Drain Current <sup>a</sup>		I <sub>DM</sub>	67			
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	50			
Single Pulse Avalanche Energy	L = 0.1 MH	E <sub>AS</sub>	125	mJ		
Maximum Power Dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	P	7.1	W		
	T <sub>C</sub> = 125 °C	P <sub>D</sub>	2.3	vv		
Operating Junction and Storage Temperature Rar	nge	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	٥C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>b</sup>	R <sub>thJA</sub>	80	°C/W	
Junction-to-Foot (Drain)		R <sub>thJF</sub>	21	0/₩	

#### Notes

a. Pulse test; pulse width  $\leq 300~\mu\text{s},$  duty cycle  $\leq 2~\%.$ 

b. When mounted on 1" square PCB (FR-4 material).

c. Parametric verification ongoing.

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0, I_D = 250 \ \mu A$		60	-	-	V
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$		3.0	3.5	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V	-	-	1.0	μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C	-	-	50	
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C	-	-	250	
On-State Drain Currenta	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	30	-	-	А
		$V_{GS} = 10 V$	I <sub>D</sub> = 6 A	-	0.0048	-	Ω
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 6 A, T <sub>J</sub> = 125 °C		0.011	-	
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 6 A, T <sub>J</sub> = 175 °C	-	0.015	-	
		$V_{GS} = 6 V$	I <sub>D</sub> = 5 A	-	0.006	-	
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 6 A		-	25	-	S
Dynamic <sup>b</sup>					•	•	
Input Capacitance	C <sub>iss</sub>		0 V V <sub>DS</sub> = 25 V, f = 1 MHz	-	2531	3165	pF
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	382	480	
Reverse Transfer Capacitance	C <sub>rss</sub>	1		-	153	195	
Total Gate Charge <sup>c</sup>	Qg			-	45	68	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{GS} = 10 V$	$V_{DS} = 30 \text{ V}, \text{ I}_{D} = 12 \text{ A}$	-	9.9	-	nC
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	1		-	11.2	-	
Gate Resistance	R <sub>g</sub>	f = 1 MHz		0.40	0.87	1.30	Ω
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			-	13	20	
Rise Time <sup>c</sup>	tr	$\label{eq:VDD} \begin{array}{l} V_{\text{DD}} = 30 \; \text{V}, \; R_{\text{L}} = 2.5 \; \Omega \\ I_{\text{D}} \cong 12 \; \text{A}, \; V_{\text{GEN}} = 10 \; \text{V}, \; R_{\text{g}} = 1 \; \Omega \end{array}$		-	12	18	ns
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	25	38	
Fall Time <sup>c</sup>	t <sub>f</sub>			-	9	14	
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>			•			
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	67	А
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = 1.7 A, V <sub>GS</sub> = 0		-	0.72	1.2	V

Notes

a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%.$ 

b. Guaranteed by design, not subject to production testing.

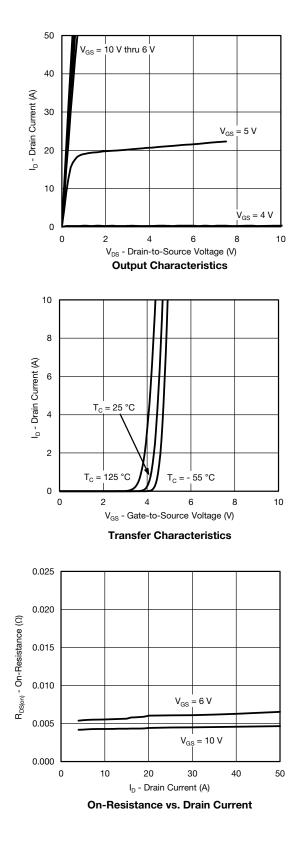
c. Independent of operating temperature.

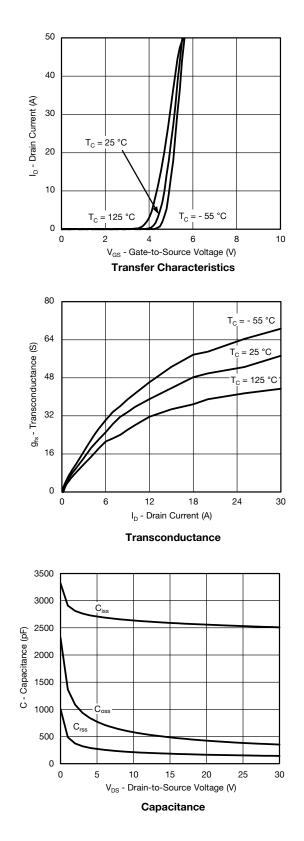
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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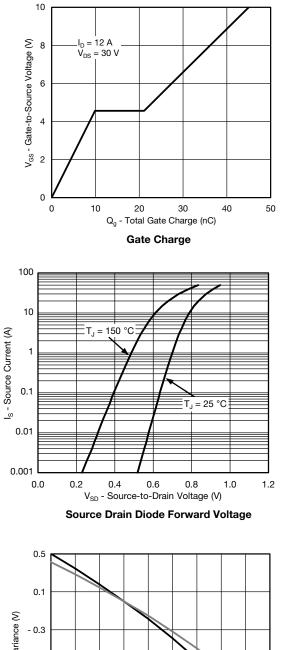
### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

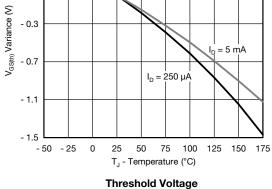


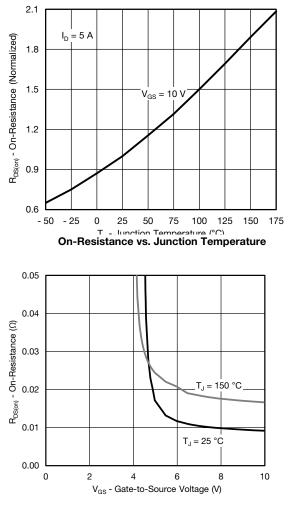




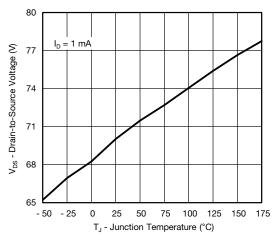
#### **TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)







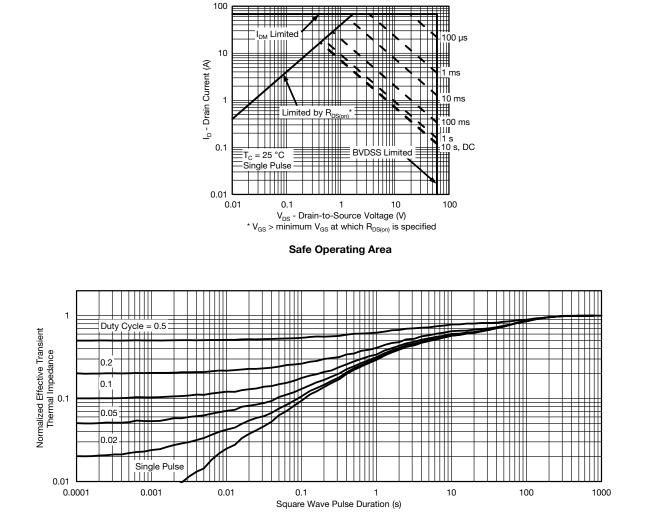
On-Resistance vs. Gate-to-Source Voltage



Drain Source Breakdown vs. Junction Temperature



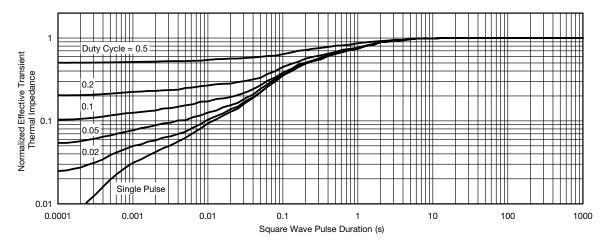
### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



#### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

The characteristics shown in the two graphs

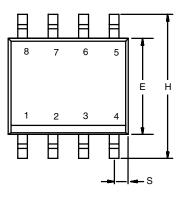
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

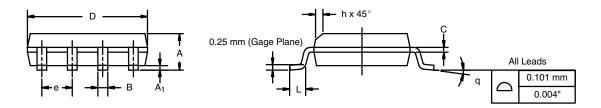
- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.



# SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012

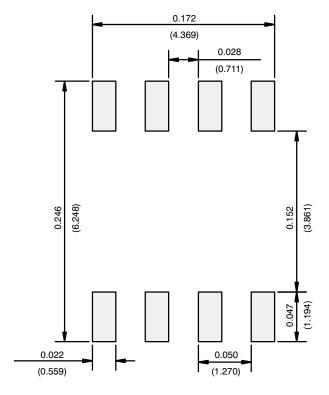




	MILLIM	IETERS	INCHES		
DIM	Min	Мах	Min	Мах	
A	1.35	1.75	0.053	0.069	
A <sub>1</sub>	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050 BSC		
н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498					



**RECOMMENDED MINIMUM PADS FOR SO-8** 



Recommended Minimum Pads Dimensions in Inches/(mm)



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